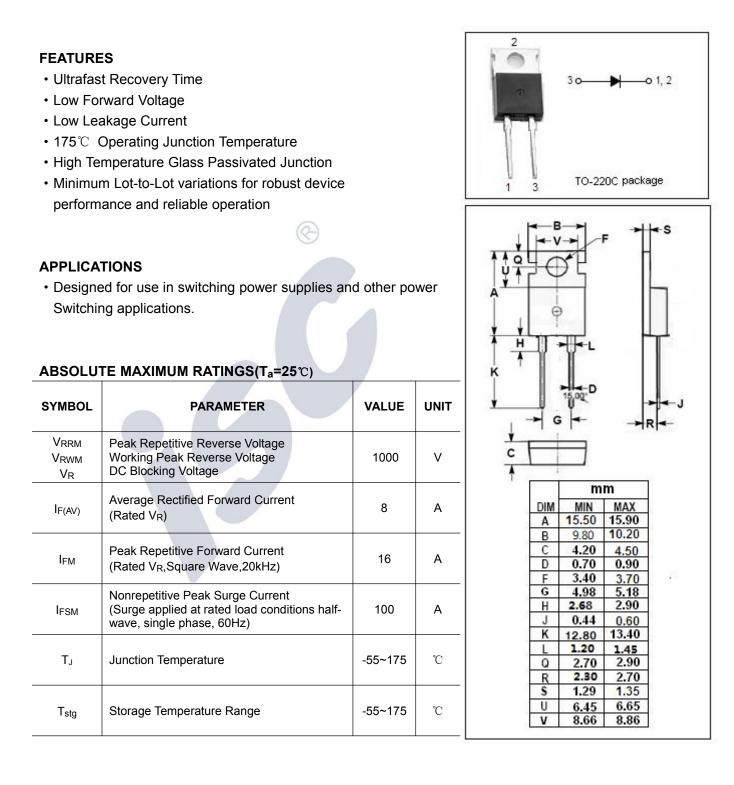


INCHANGE SEMICONDUCTOR

Ultrafast Recovery Rectifier

MUR8100E



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Ultrafast Recovery Rectifier

MUR8100E

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	2.0	°C/W

$\label{eq:expectation} \textbf{ELECTRICAL CHARACTERISTICS}(T_a = 25^{\circ}C) \quad (\text{Pulse Test: Pulse Width} = 300 \ \mu \ \text{s,Duty Cycle} \leqslant 2\%)$

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
VF	Maximum Instantaneous Forward Voltage	I⊨= 8A	1.8	V
		I⊧= 8A; T _C =150°C	1.5	V
IR	Maximum Instantaneous Reverse Current	V _{RRM} = 1000V	100	μ Α
		VRRM= 1000V;Tc=150℃	500	μA
t _{rr}	Maximum Reverse Recovery Time	I _F = 1A	85	ns

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